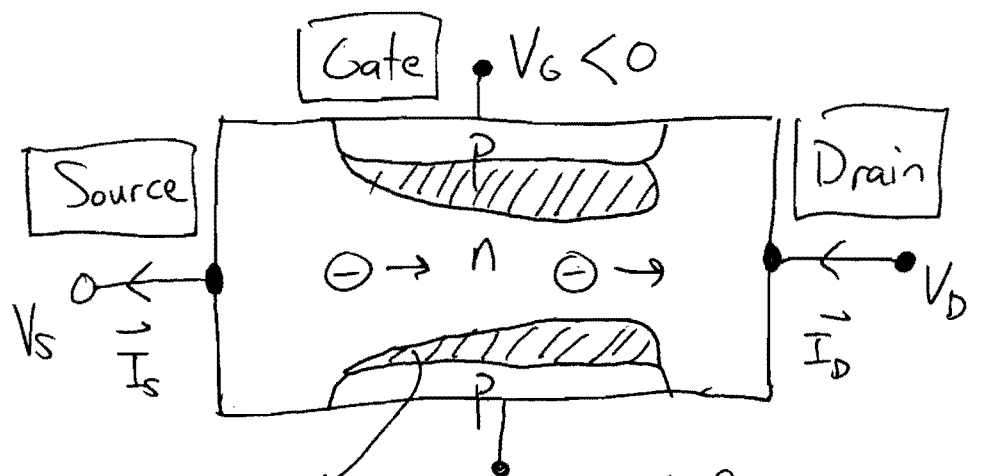
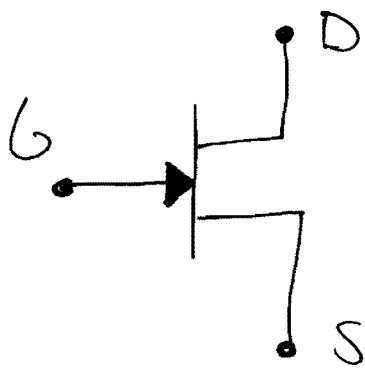


Field-Effect Transistors :

It's hard to overstate the importance of these devices in modern electronics.

JFET : (Junction Field-Effect Transistor)

Primarily n-channel because n-type materials are on average more conductive.

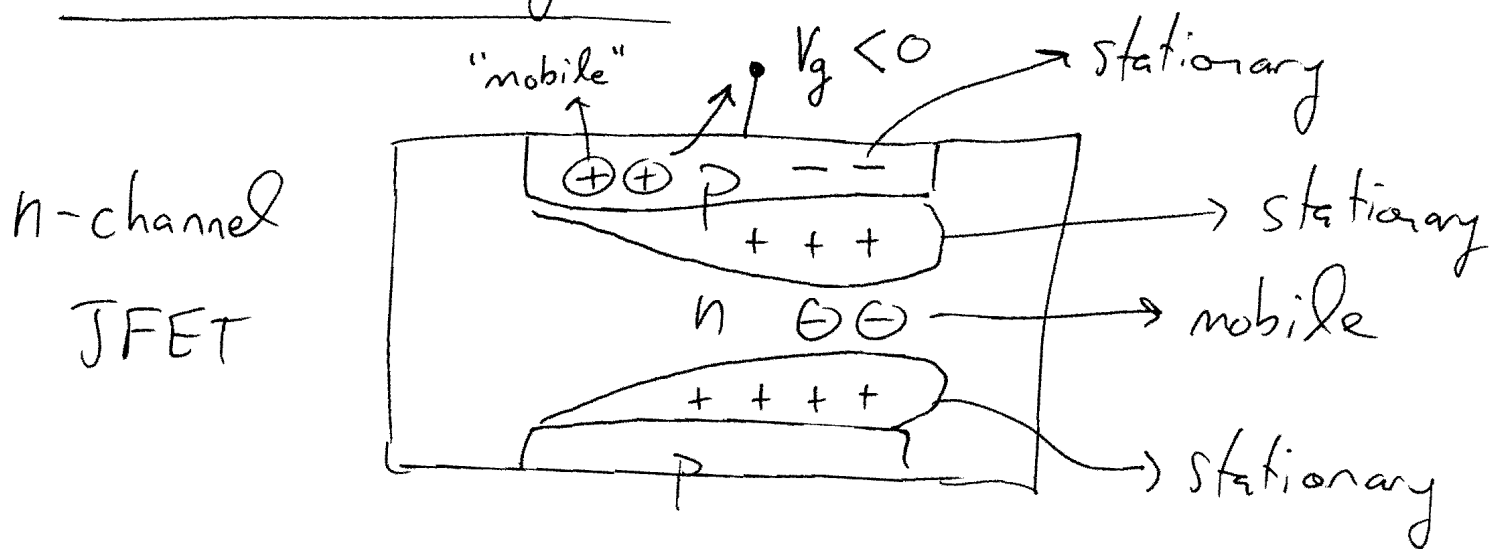


n-channel JFET

"depletion region" $V_G < 0$ (always reverse biased)

V_G is always reverse biased so current flows only in the channel. The shaded depletion region is fixed positive ionic backbone (from n-type material). By making V_G large enough (and negative) we can pinch off the \vec{I} . (1)

Depletion region

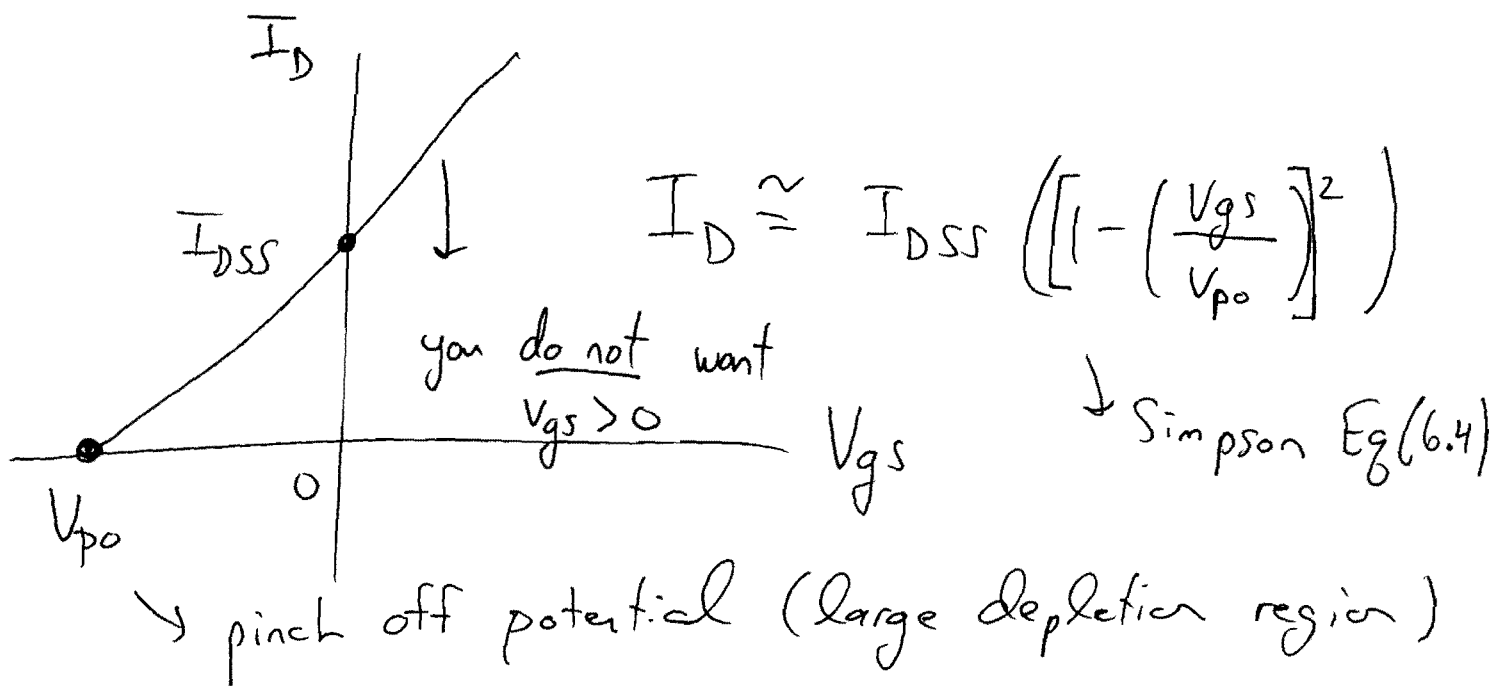


p-type = mobile \oplus , stationary $-$

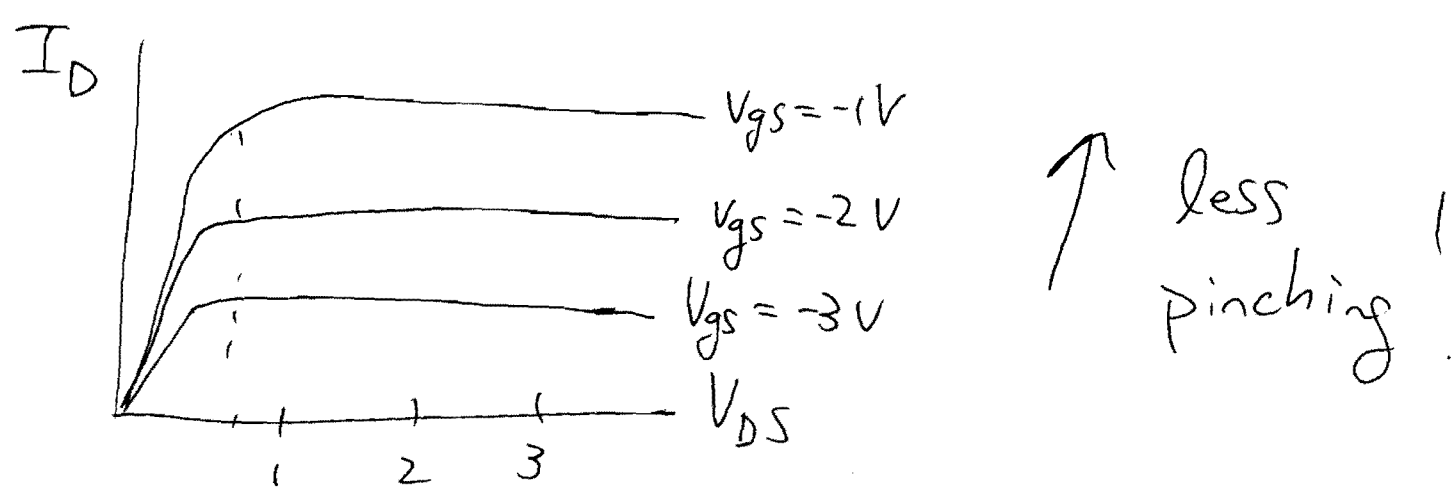
n-type = mobile \ominus , stationary $+$

① The negative V_g attracts mobile \oplus from the p region, leaving behind stationary $-$.

② These stationary $-$ regions repel mobile \ominus in the n-type regions, leaving behind stationary $+$, which is the depletion region. (1A)



I_{DSS} = un-gated channel current flow.



FET transconductance :

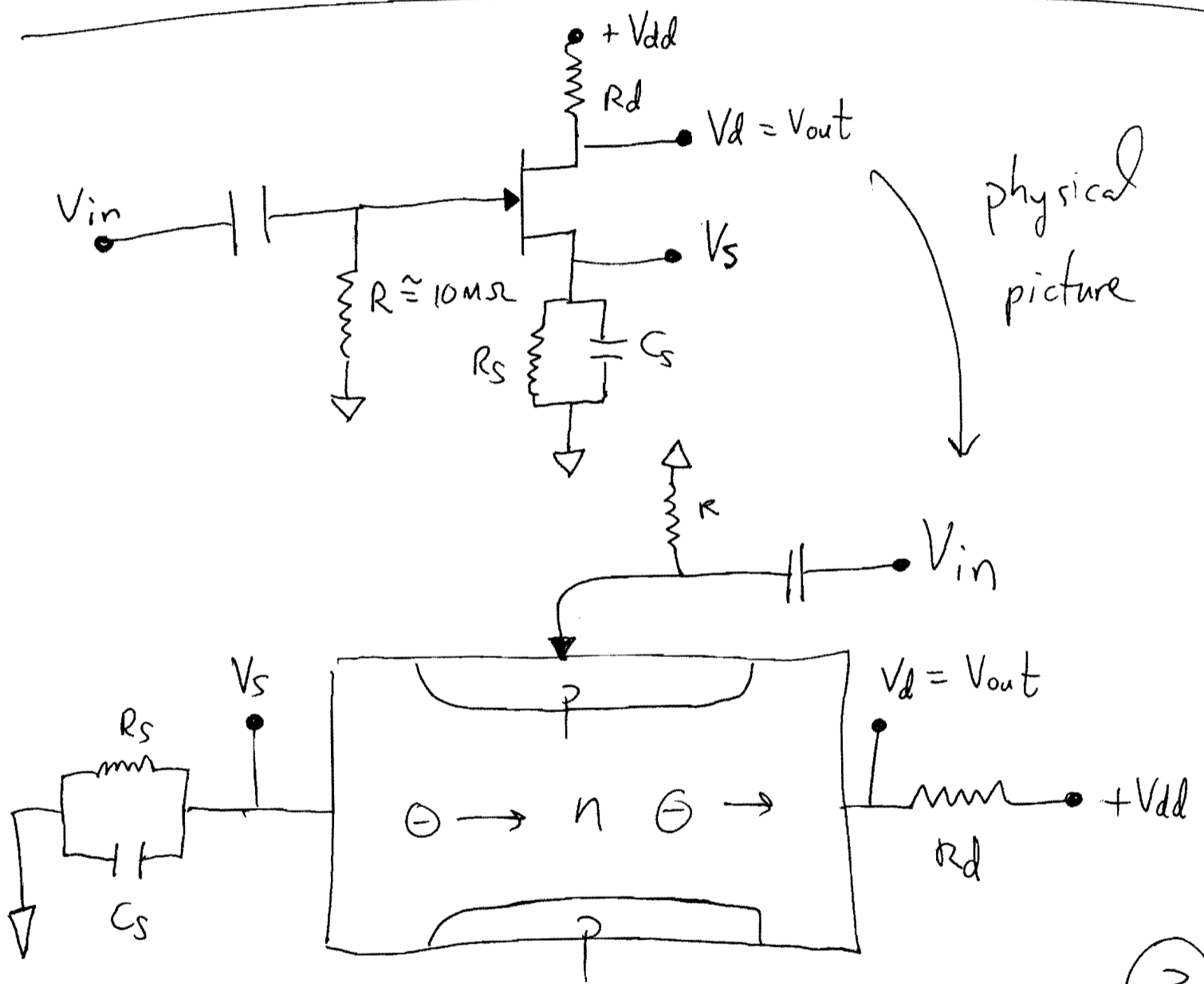
$$Y = \left(\frac{\partial I_D}{\partial V_{gs}} \right)_{V_{DS}}$$

constant drain-source potential

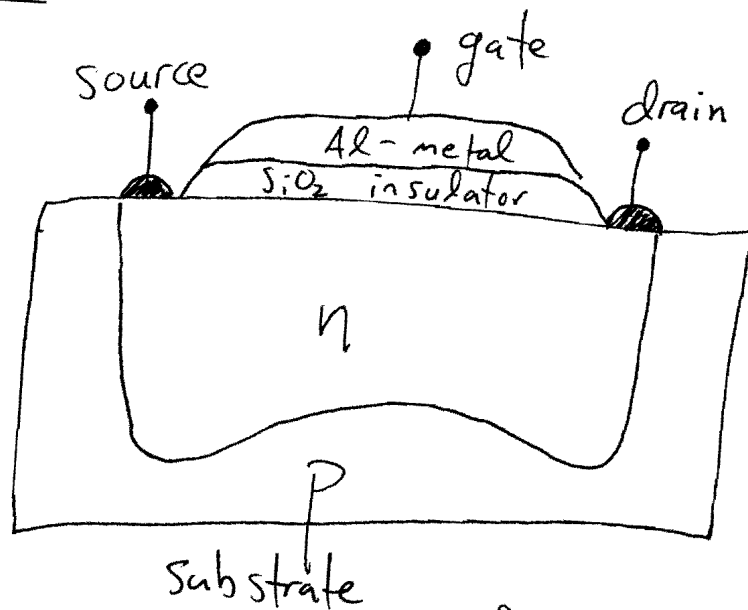
(2)

Now that I_D vs. V_{gs} is determined you want to pick the largest trans-conductance (slope) as the V_{gs} DC operating points. (Around $V_{gs} \approx -1V$)

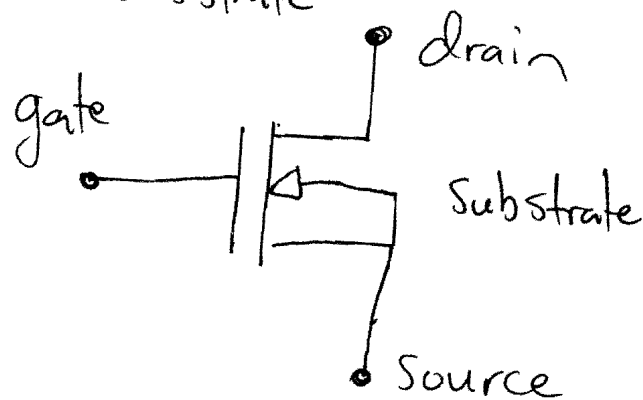
N-channel JFET Common Source Amp.



Mosfet : (Metal-oxide-semiconductor FET)

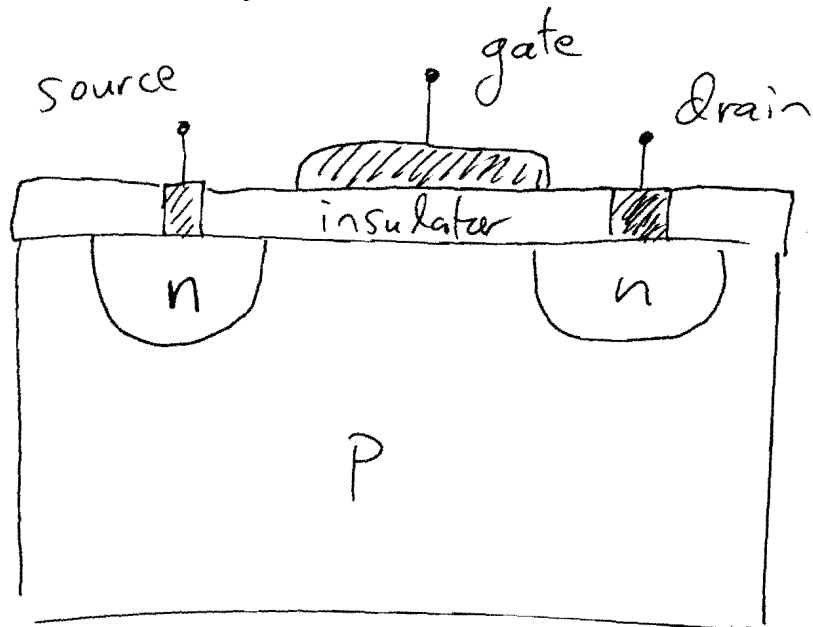
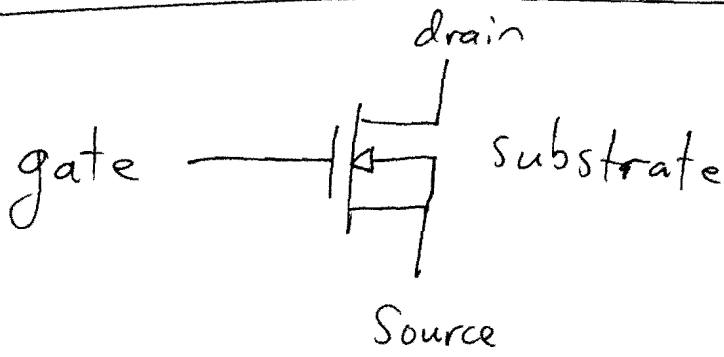


n-channel
MOSFET
"Depletion
Mode"

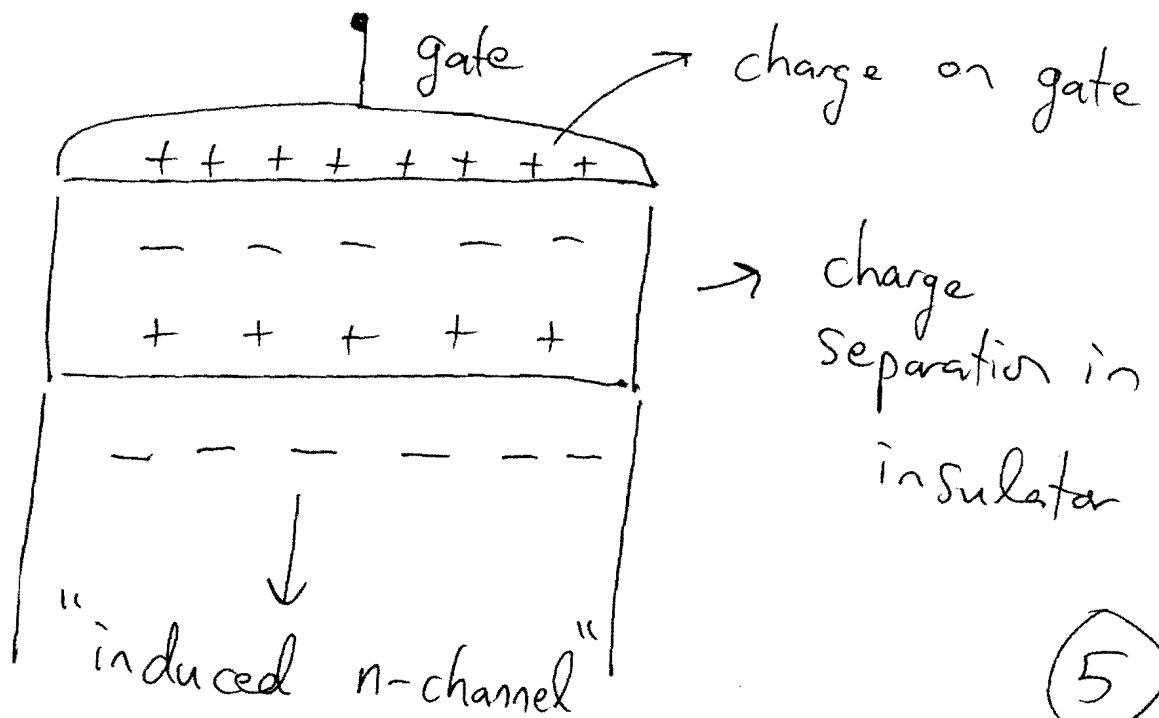


- MOSFET has smaller internal capacitance and hence, so it operates at higher frequencies than JFET.
- The gate in MOSFET is separated from the current channel by a good insulator, causing high gate-channel impedance. (4)

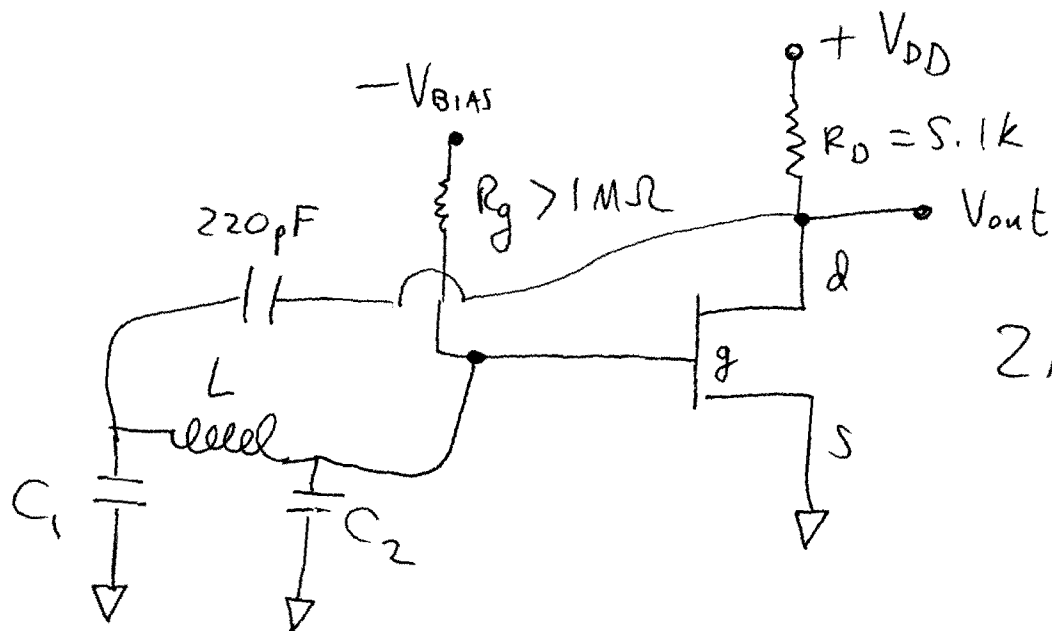
N-channel enhancement mode MOSFET :



Zoom in on gate :

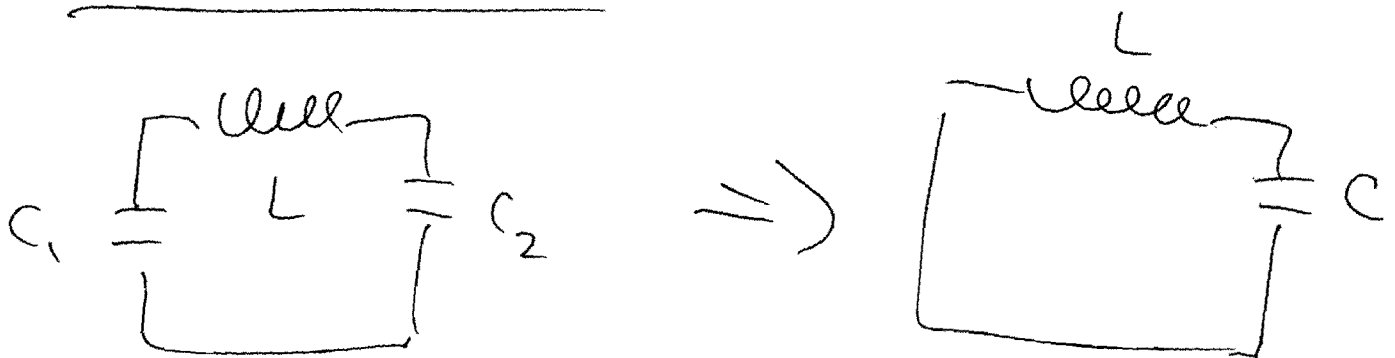


Colpitts Oscillator :



2N5459
JFET

ω_0 derivation :



$$\frac{1}{C} = \frac{1}{C_1} + \frac{1}{C_2} \rightarrow C = \frac{C_1 C_2}{C_1 + C_2}$$

$$\sum \Phi = 0 \Rightarrow \frac{Q}{C} + L \frac{dI}{dt} = 0$$

$$\text{or } \ddot{Q} = -\frac{Q}{LC}, \quad Q(t) = Q_0 e^{i\omega_0 t} \quad \left(\omega_0 = \frac{1}{\sqrt{LC}} \right) \quad (6)$$